

FORM HDP-1449 (Based on Form PTO-1449)

**PATENT AND TRADEMARK OFFICE  
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Sheet 1 of 2

ATTORNEY DOCKET No.

5077-000075/DVA

SERIAL No.

APPLICANT

Toshiya Yokogawa et al.

FILING DATE

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**U.S. PATENT DOCUMENTS**

Ref. Desig.	Examiner's Initials	Document Number	Date	Name	Class/ Subclass	(If appropriate) Filing Date
1.	TTN	6,483,100	11/2002	Williams et al.		
2.		5,091,759	02/1992	Shih et al.		
3.		5,284,782	02/1994	Jeong et al.		
4.		5,463,978	11/1995	Larkin et al.		
5.		5,492,857	02/1996	Reedy et al.		
6.		6,057,566	02/2000	Eisenbeiser et al.		
7.		5,013,685	05/1991	Chiu et al.		
8.		5,324,682	06/1994	Tserng		
9.		6,025,613	02/2000	Bito et al.		
10.		6,258,616	06/2001	Cunningham et al.		
11.		5,488,237	01/1996	Kuwata		
12.	TTN	6,380,569	04/2002	Chang et al.		

**FOREIGN PATENT DOCUMENTS**

Ref. D sig.	Examiner's Initials	Document Number	Date	Country	Class/ Subclass	Translation Yes	No
1.	TTN	05013446 A	01/22/1993	Japan		Partial	
2.	TTN	0 555 886 A2	08/18/1993	Europe			

Examiner:

Date Considered:

6/15/04

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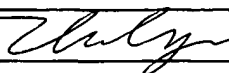
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**OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)**

R f. Desig.	Examiner's Initials	
1.	TTN	Wen-Chau Liu et al.; "Application of $\delta$ -doped Wide-Gap Collector Structure for High-Breakdown and Low-Offset voltage Transistors"; American Institute of Physics; September 7, 1998.
2.	TTN	Asen Asenov et al.; "Suppression of Random Dopant-Induced Threshold Voltage Fluctuations in Sub-0.1- $\mu$ m MOSFET's with Epitaxial and $\delta$ -Doped Channels"; IEEE Transaction on Electron Devices; Vol. 46, No. 8; August 1999.
3.	TTN	Hata (US patent Application Publication 2002/0008242 A) US class 257/79

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